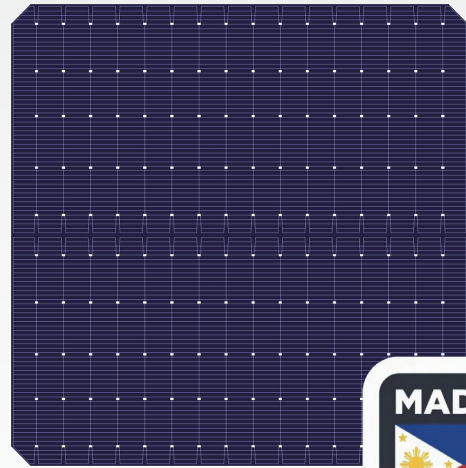
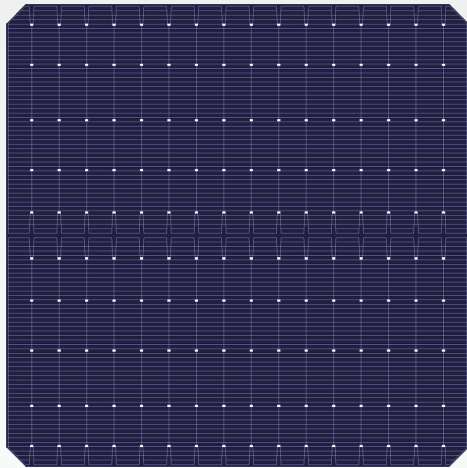


M182-N TYPE 16BB Data Sheet



High conversion efficiency with high reliability



No light-induced degradation



Uniform cell performance with stable process control



Both sides can generate electricity



Low mismatch of cell performance during encapsulation



Excellent power generation performance under low irradiation



Low hot spot effect

SOLARIS PANABO

TECHNICAL CHARACTERISTICS

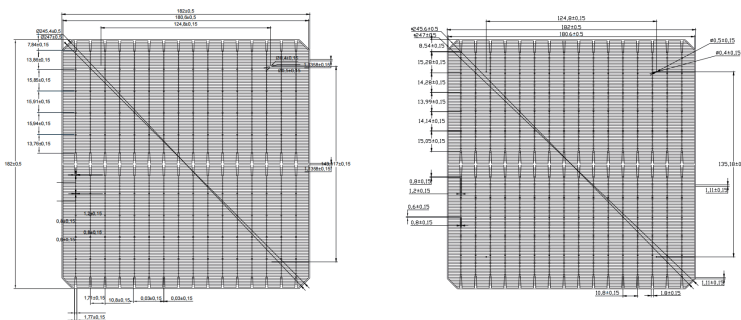
Dimension	182mm*182mm±0.5mm	TkVoltage:-0.3%/K
Thickness	140um±14um	TkCurrent:+0.048%/K
Front	16*0.036±0.02mm bus bars(silver) black anti-reflecting coating(silicon nitride)	TkPower:-0.38%/K
Back(+)	0.036±0.02mm bus bars(silver) black anti-reflecting coating(silicon nitride)	Rsh≥50Ω,Irev2≤0.5A

LIGHT INTENSITY AND RELIABILITY

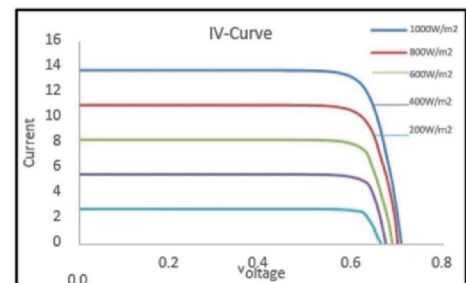
Intensity(W/m ²)	Voc	Isc
1000	1.000	1.000
900	0.996	0.903
800	0.991	0.803
600	0.988	0.602
400	0.962	0.403

The VOC(ISC) tested by 1000W/m² is the standard, and the Voc (ISC) decreases with the strong decrease in light.

PRINTING GRAPHICS



IV CURVE



WELDABILITY

Minimum peeling intensity ≥0.5N/mm

Results may vary depending on the welding ribbon, welding methods and conditions.

FRONT SIDE ELECTRICAL PERFORMANCE

Eff(%)	Pmp(W)	Vmpp(V)	Impp(A)	Voc(V)	ISC(A)	FF(%)
25.0	8.255	0.610	13.54	0.709	14.20	82.03
24.9	8.221	0.608	13.52	0.710	14.21	81.46
24.8	8.188	0.605	13.55	0.707	14.17	81.70
24.7	8.155	0.604	13.49	0.701	14.16	82.09
24.6	8.122	0.601	13.51	0.698	14.13	82.31
24.5	8.089	0.599	13.50	0.703	14.19	81.06
24.4	8.057	0.597	13.49	0.695	14.15	81.91
24.3	8.024	0.596	13.45	0.697	14.14	81.44
24.2	7.991	0.595	13.42	0.691	14.11	82.00
24.1	7.958	0.593	13.41	0.692	14.09	81.64
24.0	7.925	0.600	13.21	0.705	14.16	79.40
23.9	7.894	0.597	13.23	0.705	14.17	78.97
23.8	7.861	0.591	13.29	0.706	14.23	78.26
23.7	7.825	0.603	12.98	0.704	14.19	78.36
23.6	7.794	0.583	13.36	0.709	14.20	77.45

STC:1000W/m²,AM1.5,25 °C /Specifications and data for reference only.